# **CGD1042L**

# 1 GHz, 23 dB gain GaAs low current power doubler Rev. 1 — 10 March 2014 Produc

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

Hybrid amplifier module in a SOT115AE package, operating at a supply voltage of 24 V Direct Current (DC), employing Heterojunction Field Effect Transistor (HFET) GaAs dies.

#### 1.2 Features and benefits

- Low power consumption
- Excellent linearity
- Extremely low noise
- Excellent return loss properties
- Gain compensation over temperature
- Rugged construction
- Unconditionally stable
- Thermally optimized design
- Adjustable supply current
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

## 1.3 Applications

CATV systems operating in the 40 MHz to 1 GHz frequency range.

#### 1.4 Quick reference data

Quick reference data

Bandwidth 40 MHz to 1006 MHz;  $V_B = 24 \text{ V (DC)}$ ;  $Z_S = Z_L = 75 \Omega$ ;  $T_{mb} = 35 \text{ °C}$ ; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz		20.5	21.5	22.5	dB
		f = 1006 MHz		22	23	24	dB
СТВ	composite triple beat	V <sub>o</sub> = 51 dBmV at 550 MHz [1]	][2]	-	-61	-56	dBc
CSO	composite second-order distortion	$V_0 = 51 \text{ dBmV at } 550 \text{ MHz}$	][2]	-	-68	-64	dBc
I <sub>tot</sub>	total current	pin 4 not connected	[3]	355	375	395	mΑ
		pin 4 connected to ground	[3]	-	330	-	mΑ

- [1] 77 NTSC; [f = 54 MHz to 550 MHz]; flat  $V_0$  till 550 MHz.
- [2] pin 4 not connected.
- [3] Direct Current (DC).



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# 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	input		<b>~</b> 1 1
2, 3	common	1 5 7 9	1 4 5 9
4	I <sub>CC</sub> adjust [1]		
5	+V <sub>B</sub>		2 3 7 8
7, 8	common		aaa-011041
9	output		

<sup>[1]</sup> The total supply current can be adjusted by pin 4. Grounding of pin 4 gives the lowest supply current while floating of pin 4 gives the maximum supply current.

# 3. Ordering information

Table 3. Ordering information

Type number	Packag	Package					
	Name	Description	Version				
CGD1042L	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 × 6-32 UNC and 2 extra horizontal mounting holes; 8 gold-plated in-line leads	SOT115AE				

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_B$	supply voltage		-	30	V
$V_{i(RF)}$	RF input voltage	single tone	-	75	dBmV
I <sub>I</sub>	input current	on I <sub>CC</sub> adjust (pin 4)	-10	0	mA
T <sub>stg</sub>	storage temperature		-40	+100	°C
T <sub>mb</sub>	mounting base temperature		-20	+100	°C

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## 5. Characteristics

Table 5. Characteristics

Bandwidth 40 MHz to 1006 MHz;  $V_B = 24 \text{ V (DC)}$ ;  $Z_S = Z_L = 75 \Omega$ ;  $T_{mb} = 35 \degree C$ ; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz		20.5	21.5	22.5	dB
		f = 1006 MHz		22	23	24	dB
SL <sub>sl</sub>	slope straight line	f = 40 MHz to 1006 MHz	[1]	0.5	-	2	dB
FL	flatness of frequency response	f = 40 MHz to 1006 MHz	[2]	-	-	0.8	dB
RLin	input return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		20	-	-	dB
		f = 320 MHz to 640 MHz		18	-	-	dB
		f = 640 MHz to 870 MHz		16	-	-	dB
		f = 870 MHz to 1006 MHz		14	-	-	dB
RL <sub>out</sub>	output return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		20	-	-	dB
		f = 320 MHz to 640 MHz		19	-	-	dB
		f = 640 MHz to 870 MHz		17	-	-	dB
		f = 870 MHz to 1006 MHz		16	-	-	dB
NF	noise figure	f = 50 MHz		-	5.2	6.0	dB
		f = 1006 MHz		-	5.7	6.5	dB
Pin 4 not	connected	·		<u>'</u>			
I <sub>tot</sub>	total current		[3]	355	375	395	mA
77 NTSC	channels	·		<u>'</u>			
СТВ	composite triple beat	V <sub>o</sub> = 51 dBmV at 550 MHz	[4]	-	-61	-56	dBc
CSO	composite second-order distortion	V <sub>o</sub> = 51 dBmV at 550 MHz	[4]	-	-68	-64	dBc
		$V_0 = 51 \text{ dBmV at } 550 \text{ MHz}$	[4][8]	-	-71	-67	dBc
Xmod	cross modulation	V <sub>o</sub> = 51 dBmV at 550 MHz	[4][5]	-	-60	-	dB
79 NTSC	channels + 75 digital channels	·		<u>'</u>			
СТВ	composite triple beat	V <sub>o</sub> = 54 dBmV at 1006 MHz	[6]	-	-75	-	dBc
CSO	composite second-order distortion	V <sub>o</sub> = 54 dBmV at 1006 MHz	[6]	-	-77	-	dBc
Xmod	cross modulation	V <sub>o</sub> = 54 dBmV at 1006 MHz	[5][6]	-	-68	-	dB
CCN	carrier-to-composite noise	V <sub>o</sub> = 54 dBmV at 1006 MHz	[6]	-	62	-	dBc
74 NTSC	channels + 36 digital channels						
СТВ	composite triple beat	V <sub>o</sub> = 51 dBmV at 770 MHz	[7]	-	-65	-	dBc
CSO	composite second-order distortion	$V_o = 51 \text{ dBmV at } 770 \text{ MHz}$	[7]	-	-73	-	dBc
Xmod	cross modulation	V <sub>o</sub> = 51 dBmV at 770 MHz	[5][7]	-	-54	-	dB

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 Table 5.
 Characteristics ...continued

Bandwidth 40 MHz to 1006 MHz;  $V_B = 24 \text{ V (DC)}$ ;  $Z_S = Z_L = 75 \Omega$ ;  $T_{mb} = 35 \degree$ C; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Pin 4 con	nected to ground						
I <sub>tot</sub>	total current		[3]	-	330	-	mA
77 NTSC	channels				1		
СТВ	composite triple beat	$V_0 = 51 \text{ dBmV at } 550 \text{ MHz}$	<u>[4]</u>	-	-53	-	dBc
CSO	composite second-order distortion	$V_0 = 51 \text{ dBmV at } 550 \text{ MHz}$	<u>[4]</u>	-	-68	-	dBc
79 NTSC	channels + 75 digital channels				•		·
СТВ	composite triple beat	V <sub>o</sub> = 54 dBmV at 1006 MHz	<u>[6]</u>	-	-66	-	dBc
CSO	composite second-order distortion	V <sub>o</sub> = 54 dBmV at 1006 MHz	<u>[6]</u>	-	-77	-	dBc
CCN	carrier-to-composite noise	V <sub>o</sub> = 54 dBmV at 1006 MHz	<u>[6]</u>	-	59	-	dBc
74 NTSC	channels + 36 digital channels				'		
СТВ	composite triple beat	V <sub>o</sub> = 51 dBmV at 770 MHz	[7]	-	-59	-	dBc
CSO	composite second-order distortion	V <sub>o</sub> = 51 dBmV at 770 MHz	[7]	-	-73	-	dBc

- [1]  $G_p$  at 1003 MHz minus  $G_p$  at 40 MHz.
- [2] Flatness is defined as peak deviation to straight line.
- [3] Direct Current (DC).
- [4] 77 NTSC; [f = 54 MHz to 550 MHz]; flat  $V_0$  till 550 MHz.
- [5] Measured at 55.25 MHz.
- [6] 79 NTSC channels [f = 54 MHz to 550 MHz] + 75 digital channels [f = 550 MHz to 1006 MHz] (-6 dB offset); tilt extrapolated to 13.5 dB at 1006 MHz.
- [7] 74 NTSC channels [f = 70 MHz to 550 MHz] + 36 digital channels [f = 550 MHz to 770 MHz] (-10 dB offset); tilt = 0 dB.
- [8] Measured at 78 MHz.

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## 6. Package outline

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 8 gold-plated in-line leads

SOT115AE

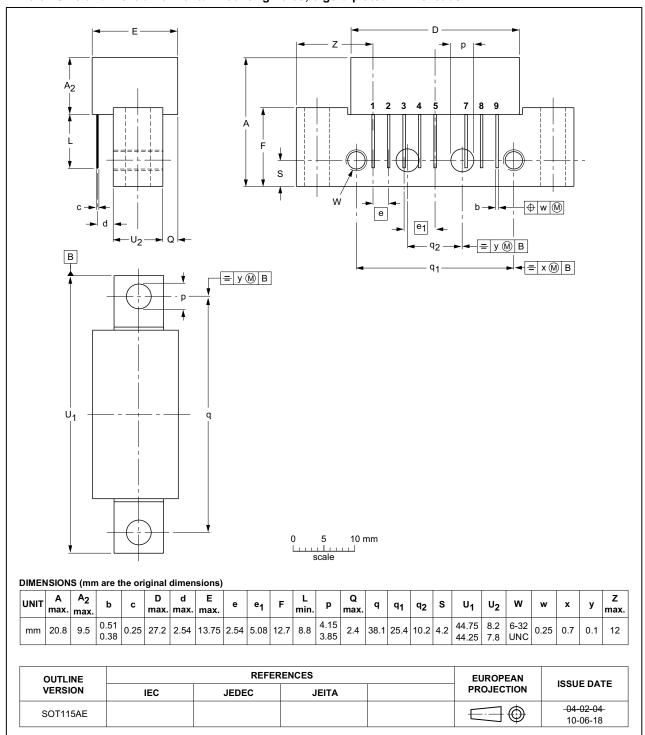


Fig 1. Package outline SOT115AE

CGD1042L

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## 7. Abbreviations

Table 6. Abbreviations

Acronym	Description
CATV	Community Antenna TeleVision
ESD	ElectroStatic Discharge
GaAs	Gallium-Arsenide
NTSC	National Television Standard Committee
RF	Radio Frequency
UNC	UNified Coarse

# 8. Revision history

## Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
CGD1042L v.1	20140310	Product data sheet	-	-

#### 1 GHz, 23 dB gain GaAs low current power doubler

## 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
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